New Release

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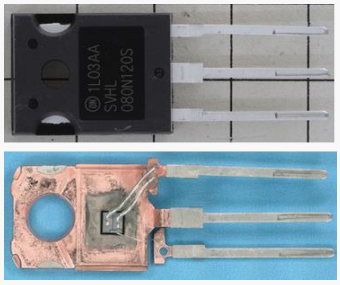
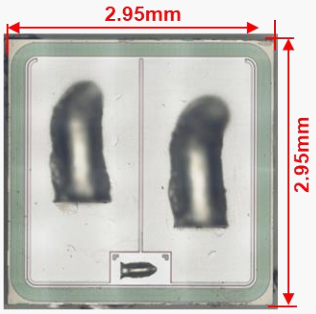
## On SEMI NVHL080N120SC1 SiC-MOSFET Die Structure and Process Analysis Reports

***February 2020.*** LTEC Corporation released detailed structure and process analysis reports of the ON-Semiconductor 1200V SiC MOSFET.




Package




Die image

**Product overview**

In March 2019, ON-Semiconductor announced production of their 1200V, Ron=80mΩ and Id=20A SiC MOSFET, promising high power density and efficiency. These features simplify the need for thermal management, BOM cost, size and weight. *The NVHL080N120SC1 is AEC-Q101 qualified for stringent automotive applications.*

**Report contents**

**SiC-MOSEFT structural analysis report**

- Package appearance, package cross-section analysis, EDX material analysis
- SiC-MOSFET die plane analysis, layout
- SiC-MOSFET die cross section analysis, cell part, die edge

**SiC-MOSFET process and device characteristics analysis report**

- Estimation of SiC-MOSFET manufacturing process flow and schematic flow. Cross section is based on structural analysis results.
- Electrical characteristics evaluation and correlation with structural parameters

**Structure analysis: $6,000 Device analysis: $4,600**

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# Structure analysis report


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